

## ABSTRACT OF THE DISCLOSURE

In a solid-state image pick-up device of Fig. 1, a plurality of photoelectric converting devices 100 having almost square light receiving regions are provided like a tetragonal grid over the surface of a semiconductor substrate and a plurality of vertical transfer sections 200 are provided corresponding to the respective photoelectric converting device strings respectively. The vertical transfer section 200 includes a vertical transfer channel and a plurality of vertical transfer electrodes provided on the upper layer of the vertical transfer channel, and the vertical transfer channel is provided in winding shape between the photoelectric converting devices 100 constituting the corresponding photoelectric converting device strings.